Schottky barrier diodes BAT81; BAT82; BAT83

FEATURES

- Low forward voltage
- High breakdown voltage
- Guard ring protected
- Hermetically-sealed leaded glass package
- Low diode capacitance.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diode with an integrated protection ring against static discharges, encapsulated in a hermetically-sealed subminiature SOD68 (DO-34) package. The diode is suitable for mounting on a 2 E (5.08 mm) pitch.

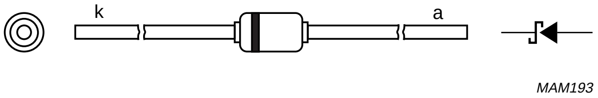

Fig.1 Simplified outline (SOD68; DO-34), pin configuration and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage				
	BAT81		–	40	V
	BAT82		–	50	V
	BAT83		–	60	V
I_F	continuous forward current		–	30	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ s; $\delta \leq 0.5$	–	150	mA
I_{FSM}	non-repetitive peak forward current	$t_p \leq 10$ ms	–	500	mA
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	125	°C